

Description

The QSM712 is designed for asymmetrical (12V to -7V) protection in multi-point data transmission application, The QSM712 replace four discrete components by integrating two 12V and two 7V TVS diodes in a single package. The QSM712 complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

Ultra low leakage: nA level

Operating voltage: 7V or 12V

Low clamping voltage

• Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 17A or 12A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: SOT-23Lead Finish: Matte Tin

Case Material: "Green" Molding Compound.
 Terminal Connections: See Diagram Below

Marking Information: See Below

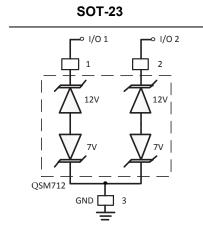
Applications

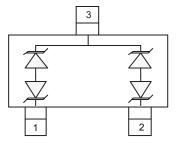
- Wireless System
- Networks
- Portable Instrumentation
- RS485 Ports

Ordering Information

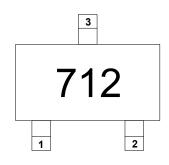
Part Number	Packaging	Reel Size	
QSM712	3000/Tape & Reel	7 inch	







Circuit diagram



712= Device code

Marking (Top View)



Absolute Maximum Ratings

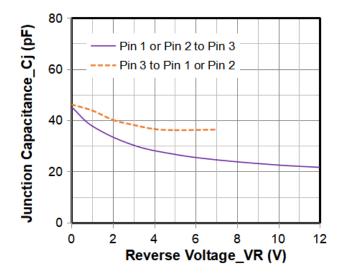
Rating	Symbol	Value	Units	
Peak Pulse Power (tp = $8/20\mu s$)	P _{PK}	300	W	
Peak Pulse Current (tp = 8/20μs), Pin 1 or 2 to Pin 3		12	_	
Peak Pulse Current (tp = $8/20\mu s$), Pin 3 to Pin 1 or 2	I _{pp}	17	Α	
ESD per IEC 61000-4-2 (Contact)	V _{ESD}	30	kV	
ESD per IEC 61000-4-2 (Air)	ESD	30		
Lead Soldering Temperature	T _L	260 (10 sec.)	°C	
Operating Temperature	T	-55 to +125	°C	
Storage Temperature	T _{STG}	-55 to +150	°C	

Electrical Characteristics (T=25°C unless otherwise specified)

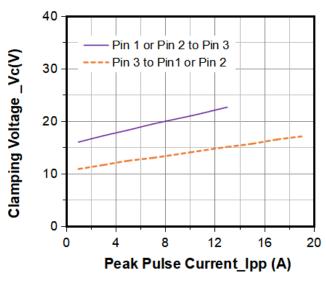
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units		
Dayarea Stand Off Valtage	V _{RWM}	Pin 1 or Pin 2 to 3				12	- V	
Reverse Stand-Off Voltage		Pin 3 to Pin 1 or 2			7	V		
Reverse Breakdown Voltage	V _{BR}	I _t = 1mA, Pin 1 or 2 to Pin 3		13.3			V	
		$I_t = 1 \text{mA}$, Pin 3 and Pi	7.5					
Reverse Leakage Current		$V_R = 12 \text{ V, Pin 1 or Pin}$	2 to 3			0.5		
	I _R	$V_R = 7 \text{ V, Pin 3 to Pin}$			0.5	μΑ		
Clamping Voltage	V _c	I _{pp} = 5A, Pin 1 or 2 to Pin 3, tp = 8/20μs			18.5	20	- V	
		$I_{pp} = 5A$, Pin 3 to Pin 1 or 2, tp = 8/20µs			12.5	14	\ \ \ \ \ \	
Clamping Voltage	V _c	I _{pp} = 12A, Pin 1 or 2 to Pin 3, tp = 8/20μs			22	26	V	
		$I_{pp} = 17A$, Pin 3 to Pin 1 or 2, $tp = 8/20 \mu s$			17	19] v	
Junction Capacitance	C _J	V 0V	Pin 1 or 2 to Pin 3		47			
		$V_R = 0V$	Pin 3 to Pin 1 or 2		47			
		V _R =12V	Pin 1 or 2 to Pin 3		22		pF	
		V _R =7V	Pin 3 to Pin 1 or 2		35			



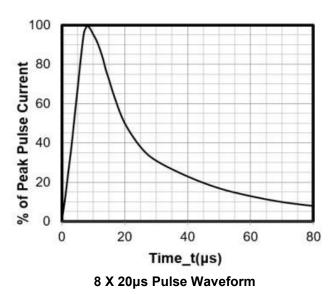
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



Junction Capacitance vs. Reverse Voltage

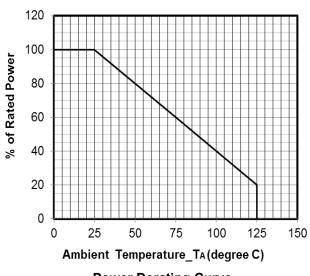


Clamping Voltage vs. Peak Pulse Current

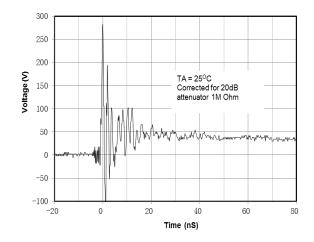


100 My 10 0.01 0.01 0.01 1 10 100 Pulse Duration_tp(µs)

Peak Pulse Power vs. Pulse Time



Power Derating Curve

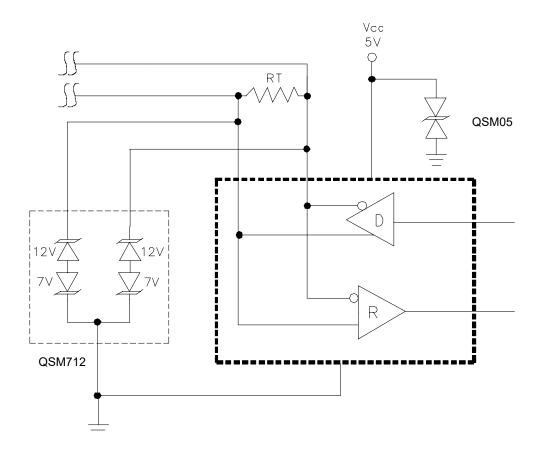


ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

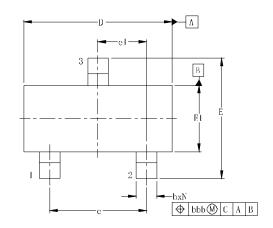


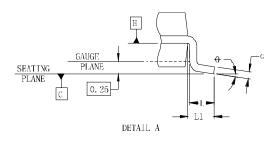
QSM712 on RS-485 Data Lines Application

EIA RS-485 specifies a ±7V ground difference between devices on the bus. This permits the bus voltage to range from +12V (5V + 7V) to -7V (0 - 7V). The QSM712 is designed to protect two RS-485 data lines in extended common mode applications. The QSM712 may be used to protect devices from transient voltages resulting from ESD, EFT, and light ning. The device is designed with asymmetrical operating voltages for optimum protection. The TVS diodes at pins 1 and 2 have a working voltage of 12volts. These pins are connected to the differential data line pairs. The TVS diodes at pin 3 have a working voltage of 7volts. Pin 3 is connected to ground. The internal TVS diodes of the QSM712 will protect the transceiver input from positive transient voltage spikes greater than 12V and negative spikes greater than 7V.









DIMENSIONS						
SYM	INCHES			MIL	LIMETE	RS
STIVI	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.035	-	0.045	0.89	-	1.15
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
С	0.003	-	0.007	80.0	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
Е	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
е	0.075			1.90BSC		
e1	0.037				0.95BSC)
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022				0.55	
N	3				3	
Ð	0°	-	8°	0°	-	8°
aaa	0.004				0.10	
bbb	0.008				0.20	

Suggested Land Pattern

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DIMENSIONS				
SYM	INCHES	MILLIMETERS		
С	0.087	2.20		
Е	0.037	0.95		
E1	0.075	1.90		
G	0.031	0.80		
X	0.039	1.00		
Υ	0.055	1.40		
Z	0.141	3.60		

Contact Information

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